

**AMENDMENTS TO THE CLAIMS:**

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

**LISTING OF CLAIMS:**

1. (Previously presented) A method of fabricating a semiconductor device, comprising the steps of:
  - (a) providing a wafer having a plurality of semiconductor elements formed thereon;
  - (b) affixing a protective tape to a first face of the wafer;
  - (c) grinding a second face of the wafer opposite to the first face;
  - (d) affixing a die bonding film to the second face of the wafer, wherein the die bonding film is affixed by pressing a laminated film of the die bonding film and a separator from the back side of the separator film so that the die bonding film faces the second face of the wafer;
  - (e) affixing a dicing tape over the die bonding film on the second face of the wafer;
  - (f) peeling off the protective tape from the first face of the wafer; and
  - (g) dicing the wafer.
2. (Original) The method according to claim 1, wherein the die bonding film contains a thermoplastic resin material.
3. (Original) The method according to claim 1, wherein the first face of the wafer is a face on which the plural semiconductor elements are formed.

4. (Original) The method according to claim 1,  
wherein the die bonding film functions as an adhesive layer at the time of die-bonding chips obtained by dicing the wafer.
5. (Original) The method according to claim 1, further comprising a step of heating the die bonding film after the step (e) and before the step (f).
6. (Original) The method according to claim 1, further comprising a step of heating the die bonding film after the step (f) and before the step (g).
7. (Original) The method according to claim 1, further comprising, after the step (e) and before the step (f), a step of heating the die bonding film for improving the adherence between the die bonding film and the wafer.
8. (Original) The method according to claim 1, further comprising, after the step (f) and before the step (g), a step of heating the die bonding film for improving the adherence between the die bonding film and the wafer.
9. (Original) The method according to claim 1, further comprising the steps of:  
heating the die bonding film to a first temperature after the step (d) and before the step (e); and  
heating the die bonding film to a second temperature higher than the first temperature after the step (e) and before the step (f).

10. (Original) The method according to claim 1, further comprising the steps of:

heating the die bonding film to a first temperature after the step (d) and before the step (e); and

heating the die bonding film to a second temperature higher than the first temperature after the step (f) and before the step (g).

11. (Original) The method according to claim 1,  
wherein, in the step (e), the dicing tape is held by a holding means disposed around the wafer, and

wherein, in the step (g), the wafer affixed to the dicing tape held by the holding means is diced.

12. (Original) The method according to claim 1,  
wherein, in the step (c), the wafer is ground to a thickness of not larger than 200  $\mu\text{m}$ .

13. (Previously presented) The method according to claim 1,  
wherein in the step (d) the laminated film of the die bonding film and the separator film is applied to the second face of the wafer in such a manner that the die bonding film faces inside; and the step (d) further includes:

peeling off the separator film; and

cutting the die bonding film along an outer periphery of the wafer.

14. – 21. (Cancelled).

22. (Previously presented) The method according to claim 1, wherein the protective tape is peeled off from the first face of the wafer after affixing the dicing tape over the die bonding film on the second face of the wafer.

23. (Previously presented) The method according to claim 1, wherein the protective tape is peeled off from the first face of the wafer after affixing the die bonding film to the second face of the wafer.

24. (Previously presented) The method according to claim 1, wherein said separator film is made of a material selected from the group consisting of polyester and poly (ethylene terephthalate).

25. (Previously presented) The method according to claim 24, wherein said die bonding film is made of thermoplastic resin material.

26. (Previously presented) The method according to claim 13, wherein the separator film is peeled off prior to said cutting the die bonding film.

27. (Previously presented) A method of fabricating a semiconductor device, comprising the steps of:

(a) providing a wafer having a plurality of semiconductor elements formed thereon;

(b) affixing a protective tape to a first face of the wafer;

- (c) grinding a second face of the wafer opposite to the first face;
  - (d) affixing a die bonding film to the second face of the wafer;
  - (e) affixing a dicing tape over the die bonding film on the second face of the wafer;
  - (f) peeling off the protective tape from the first face of the wafer; and
  - (g) dicing the wafer, and
- further comprising the steps of:
- heating the die bonding film to a first temperature after the step (d) and before the step (e); and
- heating the die bonding film to a second temperature higher than the first temperature after the step (e) and before the step (f).

28. (Previously presented) A method of fabricating a semiconductor device, comprising the steps of:

- (a) providing a wafer having a plurality of semiconductor elements formed thereon;
  - (b) affixing a protective tape to a first face of the wafer;
  - (c) grinding a second face of the wafer opposite to the first face;
  - (d) affixing a die bonding film to the second face of the wafer;
  - (e) affixing a dicing tape over the die bonding film on the second face of the wafer;
  - (f) peeling off the protective tape from the first face of the wafer; and
  - (g) dicing the wafer, and
- further comprising the steps of:

heating the die bonding film to a first temperature after the step (d) and before the step (e); and

heating the die bonding film to a second temperature higher than the first temperature after the step (f) and before the step (g).